

Kenji Nomura

List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

96
papers

17,509
citations

47
h-index

101
g-index

101
ext. papers

19,081
ext. citations

5.1
avg, IF

6.4
L-index

#	Paper	IF	Citations
96	Voltage Transfer Characteristics of CMOS-Like Inverters for Ambipolar SnO Thin-Film Transistors. <i>IEEE Electron Device Letters</i> , 2022 , 43, 52-55	4.4	2
95	Toward the Development of High-Performance p-Channel Oxide-TFTs and All-Oxide Complementary Circuits 2022 , 519-538		
94	Defects and Relevant Properties 2022 , 93-103		
93	Artificial Synapse Based on a 2D-SnO Memtransistor with Dynamically Tunable Analog Switching for Neuromorphic Computing. <i>ACS Applied Materials & Interfaces</i> , 2021 ,	9.5	9
92	Atomically Thin Tin Monoxide-Based p-Channel Thin-Film Transistor and a Low-Power Complementary Inverter. <i>ACS Applied Materials & Interfaces</i> , 2021 ,	9.5	6
91	8-3: Invited Paper: Back-Channel Defect Termination for p-Channel Oxide-TFTs. <i>Digest of Technical Papers SID International Symposium</i> , 2021 , 52, 85-88	0.5	1
90	Back-Channel Defect Termination by Sulfur for p-Channel CuO Thin-Film Transistors. <i>ACS Applied Materials & Interfaces</i> , 2020 , 12, 51581-51588	9.5	15
89	Switching Mechanism behind the Device Operation Mode in SnO-TFT. <i>Advanced Electronic Materials</i> , 2020 , 6, 2000742	6.4	13
88	Threshold switching of non-stoichiometric CuO nanowire for selector application. <i>Applied Physics Letters</i> , 2020 , 116, 023503	3.4	9
87	Frequency- and Power-Dependent Photoresponse of a Perovskite Photodetector Down to the Single-Photon Level. <i>Nano Letters</i> , 2020 , 20, 2144-2151	11.5	15
86	Hydrogen-Defect Termination in SnO for p-Channel TFTs. <i>ACS Applied Electronic Materials</i> , 2020 , 2, 1162-1168	168	23
85	Resistive switching memory effects in p-type hydrogen-treated CuO nanowire. <i>Applied Physics Letters</i> , 2020 , 117, 043502	3.4	3
84	P-2: Hydrogenated SnO for p-channel oxide Thin Film Transistor. <i>Digest of Technical Papers SID International Symposium</i> , 2020 , 51, 1315-1318	0.5	
83	Electronic Defects in Amorphous Oxide Semiconductors: A Review. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2019 , 216, 1800372	1.6	103
82	. <i>Journal of Display Technology</i> , 2014 , 10, 979-983		15
81	Roles of Hydrogen in Amorphous Oxide Semiconductor In-Ga-Zn-O: Comparison of Conventional and Ultra-High-Vacuum Sputtering. <i>ECS Journal of Solid State Science and Technology</i> , 2014 , 3, Q3085-Q3090	3.090	43
80	Examination of the ambient effects on the stability of amorphous indium-gallium-zinc oxide thin film transistors using a laser-glass-sealing technology. <i>Applied Physics Letters</i> , 2014 , 105, 133503	3.4	16

79	Surface reactivity and oxygen migration in amorphous indium-gallium-zinc oxide films annealed in humid atmosphere. <i>Applied Physics Letters</i> , 2013 , 103, 201904	3.4	26
78	P.3: 3-D Stacked Complementary TFT Devices using n-type InGaZnO and p-type F8T2 TFTs □ Operation Confirmation of NOT and NAND Logic Circuits □ <i>Digest of Technical Papers SID International Symposium</i> , 2013 , 44, 995-998	0.5	1
77	Hydrogen passivation of electron trap in amorphous In-Ga-Zn-O thin-film transistors. <i>Applied Physics Letters</i> , 2013 , 103, 202114	3.4	92
76	Operation model with carrier-density dependent mobility for amorphous InGaZnO thin-film transistors. <i>Thin Solid Films</i> , 2012 , 520, 3791-3795	2.2	11
75	Effects of low-temperature ozone annealing on operation characteristics of amorphous InGaZnO thin-film transistors. <i>Thin Solid Films</i> , 2012 , 520, 3787-3790	2.2	30
74	Photovoltaic properties of n-type amorphous InGaZnO and p-type single crystal Si heterojunction solar cells: Effects of Ga content. <i>Thin Solid Films</i> , 2012 , 520, 3808-3812	2.2	18
73	Stability and high-frequency operation of amorphous InGaZnO thin-film transistors with various passivation layers. <i>Thin Solid Films</i> , 2012 , 520, 3778-3782	2.2	69
72	Amorphous InGaZnO Dual-Gate TFTs: Current-Voltage Characteristics and Electrical Stress Instabilities. <i>IEEE Transactions on Electron Devices</i> , 2012 , 59, 1928-1935	2.9	40
71	Unusually large enhancement of thermopower in an electric field induced two-dimensional electron gas. <i>Advanced Materials</i> , 2012 , 24, 740-4	2.4	71
70	Maximum applied voltage detector using amorphous InGaZnO thin-film transistor exposed to ozone annealing. <i>Solid-State Electronics</i> , 2012 , 75, 74-76	1.7	4
69	Light Irradiation History Sensor Using Amorphous In-Ga-Zn-O Thin-Film Transistor Exposed to Ozone Annealing. <i>IEEE Electron Device Letters</i> , 2012 , 33, 384-386	4.4	6
68	Simple Analytical Model of On Operation of Amorphous InGaZnO Thin-Film Transistors. <i>IEEE Transactions on Electron Devices</i> , 2011 , 58, 3463-3471	2.9	47
67	Solid-phase epitaxial growth of (111)-oriented Si film on $\text{InGaO}_3(\text{ZnO})_5$ buffer layer. <i>Journal of Materials Science: Materials in Electronics</i> , 2011 , 22, 920-923	2.1	
66	Excimer laser crystallization of InGaZnO_4 on SiO_2 substrate. <i>Journal of Materials Science: Materials in Electronics</i> , 2011 , 22, 1694-1696	2.1	6
65	Ambipolar oxide thin-film transistor. <i>Advanced Materials</i> , 2011 , 23, 3431-4	2.4	207
64	. <i>IEEE Electron Device Letters</i> , 2011 , 32, 1695-1697	4.4	69
63	Electronic Structure and Photovoltaic Properties of n-Type Amorphous In-Ga-Zn-O and p-Type Single Crystal Si Heterojunctions. <i>Electrochemical and Solid-State Letters</i> , 2011 , 14, H346		10
62	Operation Characteristics of Thin-Film Transistors Using Very Thin Amorphous InGaZnO Channels. <i>Electrochemical and Solid-State Letters</i> , 2011 , 14, H197		43

61	Large Photoresponse in Amorphous InGaZnO and Origin of Reversible and Slow Decay. <i>Electrochemical and Solid-State Letters</i> , 2010 , 13, H324		54
60	Sputtering formation of p-type SnO thin-film transistors on glass toward oxide complimentary circuits. <i>Applied Physics Letters</i> , 2010 , 97, 072111	3.4	165
59	Three-dimensionally stacked flexible integrated circuit: Amorphous oxide/polymer hybrid complementary inverter using n-type a-InGaZnO and p-type poly-(9,9-dioctylfluorene-co-bithiophene) thin-film transistors. <i>Applied Physics Letters</i> , 2010 , 96, 263509	3.4	81
58	Intrinsic carrier mobility in amorphous InGaZnO thin-film transistors determined by combined field-effect technique. <i>Applied Physics Letters</i> , 2010 , 96, 262105	3.4	48
57	Present status of amorphous In-Ga-Zn-O thin-film transistors. <i>Science and Technology of Advanced Materials</i> , 2010 , 11, 044305	7.1	1287
56	Fabrication of Atomically Flat ScAlMgO ₄ Epitaxial Buffer Layer and Low-Temperature Growth of High-Mobility ZnO Films. <i>Crystal Growth and Design</i> , 2010 , 10, 1084-1089	3.5	5
55	Origin of definite Hall voltage and positive slope in mobility-donor density relation in disordered oxide semiconductors. <i>Applied Physics Letters</i> , 2010 , 96, 122103	3.4	121
54	Comprehensive studies on the stabilities of a-In-Ga-Zn-O based thin film transistor by constant current stress. <i>Thin Solid Films</i> , 2010 , 518, 3012-3016	2.2	45
53	Steady-state photoconductivity of amorphous InGaZnO. <i>Thin Solid Films</i> , 2010 , 518, 3000-3003	2.2	16
52	Fabrication of GaN epitaxial thin film on InGaZnO ₄ single-crystalline buffer layer. <i>Thin Solid Films</i> , 2010 , 518, 2996-2999	2.2	3
51	Device characteristics improvement of a-InGaZnO TFTs by low-temperature annealing. <i>Thin Solid Films</i> , 2010 , 518, 3017-3021	2.2	80
50	Field-modulated thermopower in SrTiO ₃ -based field-effect transistors with amorphous 12CaO·7Al ₂ O ₃ glass gate insulator. <i>Applied Physics Letters</i> , 2009 , 95, 113505	3.4	48
49	Amorphous InGaZnO coplanar homojunction thin-film transistor. <i>Applied Physics Letters</i> , 2009 , 94, 133502	3.4	150
48	Interactive radical dimers in photoconductive organic thin films. <i>Angewandte Chemie - International Edition</i> , 2009 , 48, 4022-4	16.4	50
47	Large domain growth of GaN epitaxial films on lattice-matched buffer layer ScAlMgO ₄ . <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2009 , 161, 66-70	3.1	5
46	Tin monoxide as an s-orbital-based p-type oxide semiconductor: Electronic structures and TFT application. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2009 , 206, 2187-2191	1.6	185
45	Effects of post-annealing on (110) Cu ₂ O epitaxial films and origin of low mobility in Cu ₂ O thin-film transistor. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2009 , 206, 2192-2197	1.6	59
44	Amorphous InGaZn-O thin-film transistor with coplanar homojunction structure. <i>Thin Solid Films</i> , 2009 , 518, 1309-1313	2.2	50

43	Origins of High Mobility and Low Operation Voltage of Amorphous Oxide TFTs: Electronic Structure, Electron Transport, Defects and Doping. <i>Journal of Display Technology</i> , 2009 , 5, 273-288		371
42	Electronic Structures Above Mobility Edges in Crystalline and Amorphous In-Ga-Zn-O: Percolation Conduction Examined by Analytical Model. <i>Journal of Display Technology</i> , 2009 , 5, 462-467		185
41	Anisotropic carrier transport properties in layered cobaltate epitaxial films grown by reactive solid-phase epitaxy. <i>Applied Physics Letters</i> , 2009 , 94, 152105	3-4	19
40	Trap densities in amorphous-InGaZnO4 thin-film transistors. <i>Applied Physics Letters</i> , 2008 , 92, 133512	3-4	254
39	Factors controlling electron transport properties in transparent amorphous oxide semiconductors. <i>Journal of Non-Crystalline Solids</i> , 2008 , 354, 2796-2800	3-9	152
38	p-channel thin-film transistor using p-type oxide semiconductor, SnO. <i>Applied Physics Letters</i> , 2008 , 93, 032113	3-4	491
37	Modeling of amorphous InGaZnO4 thin film transistors and their subgap density of states. <i>Applied Physics Letters</i> , 2008 , 92, 133503	3-4	289
36	Epitaxial growth of high mobility Cu2O thin films and application to p-channel thin film transistor. <i>Applied Physics Letters</i> , 2008 , 93, 202107	3-4	193
35	Photofield-effect in amorphous In-Ga-Zn-O (a-IGZO) thin-film transistors. <i>Journal of Information Display</i> , 2008 , 9, 21-29	4-1	82
34	Optical and Carrier Transport Properties of Cosputtered ZnInSn Films and Their Applications to TFTs. <i>Journal of the Electrochemical Society</i> , 2008 , 155, H390	3-9	57
33	Subgap states in transparent amorphous oxide semiconductor, InGaZnO, observed by bulk sensitive x-ray photoelectron spectroscopy. <i>Applied Physics Letters</i> , 2008 , 92, 202117	3-4	268
32	Defect passivation and homogenization of amorphous oxide thin-film transistor by wet O2 annealing. <i>Applied Physics Letters</i> , 2008 , 93, 192107	3-4	243
31	Amorphous oxide channel TFTs. <i>Thin Solid Films</i> , 2008 , 516, 1516-1522	2-2	155
30	Specific contact resistances between amorphous oxide semiconductor InGaZnO and metallic electrodes. <i>Thin Solid Films</i> , 2008 , 516, 5899-5902	2-2	171
29	Control of carrier concentration and surface flattening of CuGaO2 epitaxial films for a p-channel transparent transistor. <i>Thin Solid Films</i> , 2008 , 516, 5790-5794	2-2	32
28	Fabrication of ScAlMgO4 epitaxial thin films using ScGaO3(ZnO)m buffer layers and its application to lattice-matched buffer layer for ZnO epitaxial growth. <i>Thin Solid Films</i> , 2008 , 516, 5842-5846	2-2	4
27	Giant thermoelectric Seebeck coefficient of a two-dimensional electron gas in SrTiO3. <i>Nature Materials</i> , 2007 , 6, 129-34	27	794
26	Fast Thin-Film Transistor Circuits Based on Amorphous Oxide Semiconductor. <i>IEEE Electron Device Letters</i> , 2007 , 28, 273-275	4-4	104

25	Combinatorial approach to thin-film transistors using multicomponent semiconductor channels: An application to amorphous oxide semiconductors in InGaZnO system. <i>Applied Physics Letters</i> , 2007 , 90, 242114	3.4	200
24	Epitaxial film growth, optical, electrical, and magnetic properties of layered oxide In ₃ FeTi ₂ O ₁₀ . <i>Journal of Applied Physics</i> , 2007 , 101, 103714	2.5	6
23	Growth, structure and carrier transport properties of Ga ₂ O ₃ epitaxial film examined for transparent field-effect transistor. <i>Thin Solid Films</i> , 2006 , 496, 37-41	2.2	142
22	Epitaxial film growth and superconducting behavior of sodium-cobalt oxyhydrate, Na _x CoO ₂ ·yH ₂ O (x approximately 0.3, y approximately 1.3). <i>Inorganic Chemistry</i> , 2006 , 45, 1894-6	5.1	13
21	High-mobility thin-film transistor with amorphous InGaZnO ₄ channel fabricated by room temperature rf-magnetron sputtering. <i>Applied Physics Letters</i> , 2006 , 89, 112123	3.4	944
20	Amorphous Oxide Semiconductors for High-Performance Flexible Thin-Film Transistors. <i>Japanese Journal of Applied Physics</i> , 2006 , 45, 4303-4308	1.4	589
19	Self-Adjusted, Three-Dimensional Lattice-Matched Buffer Layer for Growing ZnO Epitaxial Film: Homologous Series Layered Oxide, InGaO ₃ (ZnO) ₅ . <i>Crystal Growth and Design</i> , 2006 , 6, 2451-2456	3.5	18
18	Growth and structure of heteroepitaxial thin films of homologous compounds RAO ₃ (MO) _m by reactive solid-phase epitaxy: Applicability to a variety of materials and epitaxial template layers. <i>Thin Solid Films</i> , 2006 , 496, 64-69	2.2	13
17	Device applications of transparent oxide semiconductors: Excitonic blue LED and transparent flexible TFT. <i>Journal of Electroceramics</i> , 2006 , 17, 267-275	1.5	41
16	Field-Induced Current Modulation in Nanoporous Semiconductor, Electron-Doped 12CaO \cdot 7Al ₂ O ₃ . <i>Chemistry of Materials</i> , 2005 , 17, 6311-6316	9.6	39
15	Carrier transport and electronic structure in amorphous oxide semiconductor, a-InGaZnO ₄ . <i>Thin Solid Films</i> , 2005 , 486, 38-41	2.2	385
14	Growth of epitaxial ZnO thin films on lattice-matched buffer layer: Application of InGaO ₃ (ZnO) ₆ single-crystalline thin film. <i>Thin Solid Films</i> , 2005 , 486, 28-32	2.2	13
13	????????? TFT ?????????????????????????????????? TFT ?. <i>Seikei-Kakou</i> , 2005 , 17, 588-592	0	
12	Growth mechanism for single-crystalline thin film of InGaO ₃ (ZnO) ₅ by reactive solid-phase epitaxy. <i>Journal of Applied Physics</i> , 2004 , 95, 5532-5539	2.5	54
11	Room-temperature fabrication of transparent flexible thin-film transistors using amorphous oxide semiconductors. <i>Nature</i> , 2004 , 432, 488-92	50.4	5517
10	All oxide transparent MISFET using high-k dielectrics gates. <i>Microelectronic Engineering</i> , 2004 , 72, 294-298	5	18
9	Carrier transport in transparent oxide semiconductor with intrinsic structural randomness probed using single-crystalline InGaO ₃ (ZnO) ₅ films. <i>Applied Physics Letters</i> , 2004 , 85, 1993-1995	3.4	229
8	Electron transport in InGaO ₃ (ZnO) _m (m=integer) studied using single-crystalline thin films and transparent MISFETs. <i>Thin Solid Films</i> , 2003 , 445, 322-326	2.2	11

7	Frontier of transparent oxide semiconductors. <i>Solid-State Electronics</i> , 2003 , 47, 2261-2267	1.7	123
6	Thin-film transistor fabricated in single-crystalline transparent oxide semiconductor. <i>Science</i> , 2003 , 300, 1269-72	33.3	1534
5	Novel film growth technique of single crystalline $\text{In}_2\text{O}_3(\text{ZnO})_m$ (m =integer) homologous compound. <i>Thin Solid Films</i> , 2002 , 411, 147-151	2.2	35
4	Orientation control of zinc oxide films by pulsed current electrolysis. <i>Journal of Crystal Growth</i> , 2002 , 235, 224-228	1.6	22
3	Preparation of Zinc Oxide Thin Films by Pulsed Current Electrolysis. <i>Journal of the Electrochemical Society</i> , 2002 , 149, F76	3.9	20
2	In situ Observation of the Crystallization Process of Ferroelectric Thin Films by Raman Microspectroscopy. <i>Japanese Journal of Applied Physics</i> , 2000 , 39, 5247-5251	1.4	15
1	Recent progress of oxide-TFT-based inverter technology. <i>Journal of Information Display</i> , 1-19	4.1	9